Preferred Devices

# **Bias Resistor Transistor**

# PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SC–70/SOT–323 package which is designed for low power surface mount applications.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- The SC-70/SOT-323 package can be soldered using wave or reflow. The modified gull-winged leads absorb thermal stress during soldering eliminating the possibility of damage to the die.
- Available in 8 mm embossed tape and reel Use the Device Number to order the 7 inch/3000 unit reel. Replace "T1" with "T3" in the Device Number to order the 13 inch/10,000 unit reel.

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)

| Rating   | Symbol           | Value      | Unit        |
|--|------------------|------------|-------------|
| Collector-Base Voltage   | V <sub>CBO</sub> | 50         | Vdc         |
| Collector-Emitter Voltage  | V <sub>CEO</sub> | 50         | Vdc         |
| Collector Current  | Ι <sub>C</sub>   | 100        | mAdc        |
| Total Power Dissipation<br>@ $T_A = 25^{\circ}C^{(1.)}$<br>Derate above 25°C | PD               | 150<br>1.2 | mW<br>mW/°C |

#### DEVICE MARKING AND RESISTOR VALUES

| Device                    | Marking | R1 (K) | R2 (K) | Shipping         |
|---------------------------|---------|--------|--------|------------------|
| MUN5111T1                 | 6A      | 10     | 10     | 3000/Tape & Reel |
| MUN5112T1                 | 6B      | 22     | 22     |                  |
| MUN5113T1                 | 6C      | 47     | 47     |                  |
| MUN5114T1                 | 6D      | 10     | 47     |                  |
| MUN5115T1 <sup>(2.)</sup> | 6E      | 10     | ∞      |                  |
| MUN5116T1 <sup>(2.)</sup> | 6F      | 4.7    | ~      |                  |
| MUN5130T1 <sup>(2.)</sup> | 6G      | 1.0    | 1.0    |                  |
| MUN5131T1 <sup>(2.)</sup> | 6H      | 2.2    | 2.2    |                  |
| MUN5132T1 <sup>(2.)</sup> | 6J      | 4.7    | 4.7    |                  |
| MUN5133T1 <sup>(2.)</sup> | 6K      | 4.7    | 47     |                  |
| MUN5134T1 <sup>(2.)</sup> | 6L      | 22     | 47     |                  |
| MUN5135T1 <sup>(2.)</sup> | 6M      | 2.2    | 47     |                  |

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

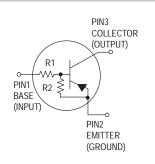
2. New devices. Updated curves to follow in subsequent data sheets.



#### **ON Semiconductor**

http://onsemi.com

## PNP SILICON BIAS RESISTOR TRANSISTORS





CASE 419 SC-70/SOT-323 STYLE 3

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

| Characteristic   | Symbol                            | Max         | Unit      |
|--|-----------------------------------|-------------|-----------|
| Thermal Resistance — Junction to Ambient (surface mounted)         | $R_{\theta JA}$                   | 833         | °C/W      |
| Operating and Storage Temperature Range                            | T <sub>J</sub> , T <sub>stg</sub> | -65 to +150 | °C        |
| Maximum Temperature for Soldering Purposes,<br>Time in Solder Bath | ΤL                                | 260<br>10   | °C<br>Sec |

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$  unless otherwise noted)

| Characteristic      | Symbol | Min | Тур | Max | Unit |
|---------------------|--------|-----|-----|-----|------|
| OFE CHARACTERISTICS |        |     |     |     |      |

| OFF CHARACTERISTICS  |   |                      |    |   |   |      |
|--|---|----------------------|----|---|---|------|
| Collector–Base Cutoff Current ( $V_{CB} = 50 \text{ V}, I_E = 0$ )           |   | I <sub>CBO</sub>     | _  | — | 100   | nAdc |
| Collector–Emitter Cutoff Current ( $V_{CE} = 50 \text{ V}, I_B = 0$ )        |   | I <sub>CEO</sub>     | —  | — | 500   | nAdc |
| Emitter–Base Cutoff Current<br>(V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0) | MUN5111T1<br>MUN5112T1<br>MUN5113T1<br>MUN5114T1<br>MUN5115T1<br>MUN5130T1<br>MUN5131T1<br>MUN5132T1<br>MUN5133T1<br>MUN5134T1<br>MUN5135T1 | I <sub>EBO</sub>     |    |   | 0.5<br>0.2<br>0.1<br>0.9<br>1.9<br>4.3<br>2.3<br>1.5<br>0.18<br>0.13<br>0.2 | mAdc |
| Collector–Base Breakdown Voltage (I <sub>C</sub> = 10                        | 0 μA, I <sub>E</sub> = 0)   | V <sub>(BR)CBO</sub> | 50 |   | —   | Vdc  |
| Collector–Emitter Breakdown Voltage (3.) (I                                  | $_{\rm C}$ = 2.0 mA, I <sub>B</sub> = 0)  | V <sub>(BR)CEO</sub> | 50 | — | —   | Vdc  |

#### ON CHARACTERISTICS (3.)

| DC Current Gain   | MUN5111T1             | h <sub>FE</sub>      | 35  | 60  | —    |     |
|---|-----------------------|----------------------|-----|-----|------|-----|
| (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 5.0 mA)   | MUN5112T1             |                      | 60  | 100 | —    |     |
|   | MUN5113T1             |                      | 80  | 140 | —    |     |
|   | MUN5114T1             |                      | 80  | 140 | —    |     |
|   | MUN5115T1             |                      | 160 | 250 | —    |     |
|   | MUN5116T1             |                      | 160 | 250 | —    |     |
|   | MUN5130T1             |                      | 3.0 | 5.0 | —    |     |
|   | MUN5131T1             |                      | 8.0 | 15  | —    |     |
|   | MUN5132T1             |                      | 15  | 27  | —    |     |
|   | MUN5133T1             |                      | 80  | 140 | —    |     |
|   | MUN5134T1             |                      | 80  | 130 | —    |     |
|   | MUN5135T1             |                      | 80  | 140 | —    |     |
| $      Collector-Emitter Saturation Voltage (I_C = 1 \\ (I_C = 10 \text{ mA}, I_B = 5 \text{ mA}) \text{ MUN5130T1/MI} \\ (I_C = 10 \text{ mA}, I_B = 1 \text{ mA}) \text{ MUN5115T1/MI} \\ \text{ MUN5132T1/MUN5133T1/MUN} $ | JN5131T1<br>JN5116T1/ | V <sub>CE(sat)</sub> | _   |     | 0.25 | Vdc |
| Output Voltage (on)   |                       | Vol                  |     |     |      | Vdc |
| $(V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$  | MUN5111T1             | 01                   | l — | —   | 0.2  |     |
|   | MUN5112T1             |                      | _   | _   | 0.2  |     |
|   | MUN5114T1             |                      | _   | —   | 0.2  |     |
|   | MUN5115T1             |                      | _   | —   | 0.2  |     |
|   | MUN5116T1             |                      | _   | —   | 0.2  |     |
|   | MUN5130T1             |                      | _   | —   | 0.2  |     |
|   | MUN5131T1             |                      | -   | —   | 0.2  |     |
|   | MUN5132T1             |                      | -   | —   | 0.2  |     |
|   | MUN5133T1             |                      | -   | —   | 0.2  |     |
|   | MUN5134T1             |                      | -   | —   | 0.2  |     |
|   | MUN5135T1             |                      | -   | —   | 0.2  |     |
| $(V_{CC} = 5.0 \text{ V}, V_B = 3.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$  | MUN5113T1             |                      | -   | —   | 0.2  |     |

3. Pulse Test: Pulse Width < 300  $\mu s,$  Duty Cycle < 2.0%

|                                       | Characteristic   |                                | Min  | Тур  | Мах   | Unit |
|---------------------------------------|--|--------------------------------|--|--|---|------|
| $(V_{CC} = 5.0 \text{ V}, \text{ V})$ |  | V <sub>OH</sub>                | 4.9  | _  | _   | Vdc  |
| Input Resistor                        | MUN5111T1<br>MUN5112T1<br>MUN5113T1<br>MUN5114T1<br>MUN5115T1<br>MUN5130T1<br>MUN5131T1<br>MUN5132T1<br>MUN5133T1<br>MUN5133T1<br>MUN5134T1<br>MUN5135T1 | R1                             | 7.0<br>15.4<br>32.9<br>7.0<br>7.0<br>3.3<br>0.7<br>1.5<br>3.3<br>3.3<br>15.4<br>1.54 | 10<br>22<br>47<br>10<br>4.7<br>1.0<br>2.2<br>4.7<br>4.7<br>22<br>2.2 | 13<br>28.6<br>61.1<br>13<br>6.1<br>1.3<br>2.9<br>6.1<br>6.1<br>28.6<br>2.86 | kΩ   |
| Resistor Ratio                        | MUN5111T1/MUN5112T1/MUN5113T1<br>MUN5114T1<br>MUN5115T1/MUN5116T1<br>MUN5130T1/MUN5131T1/MUN5132T1<br>MUN5133T1<br>MUN5134T1<br>MUN5135T1                | R <sub>1</sub> /R <sub>2</sub> | 0.8<br>0.17<br><br>0.8<br>0.055<br>0.38<br>0.038                                     | 1.0<br>0.21<br>—<br>1.0<br>0.1<br>0.47<br>0.047                      | 1.2<br>0.25<br>—<br>1.2<br>0.185<br>0.56<br>0.056                           |      |

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

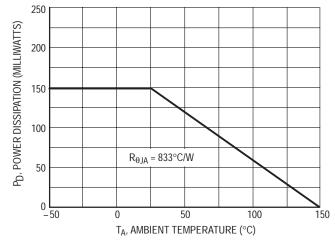
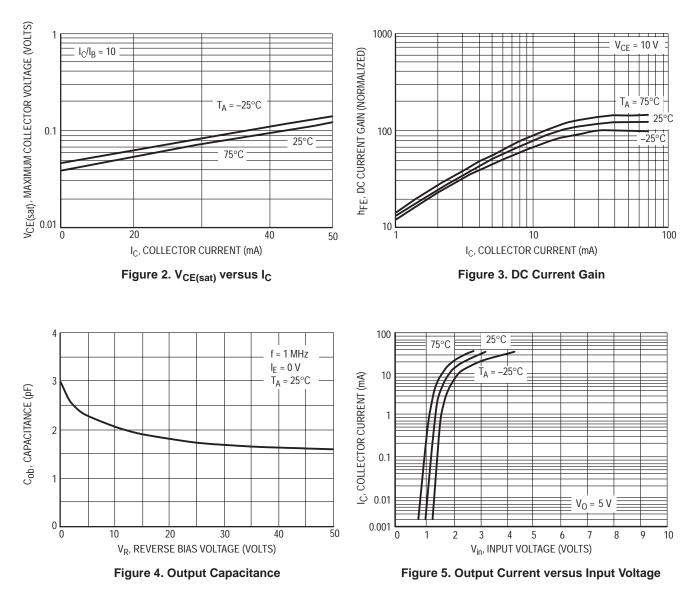


Figure 1. Derating Curve

#### TYPICAL ELECTRICAL CHARACTERISTICS — MUN5111T1



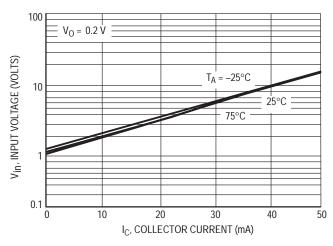
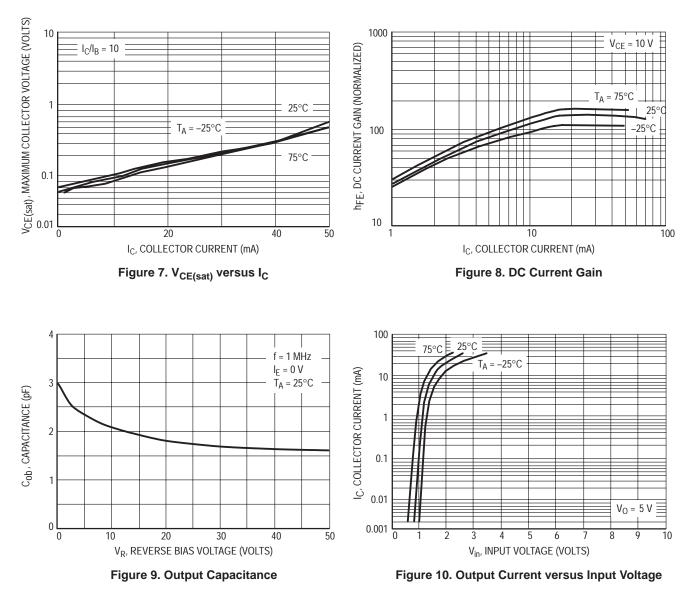


Figure 6. Input Voltage versus Output Current





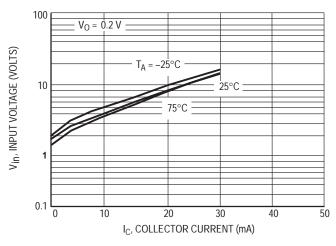


Figure 11. Input Voltage versus Output Current

#### TYPICAL ELECTRICAL CHARACTERISTICS - MUN5113T1

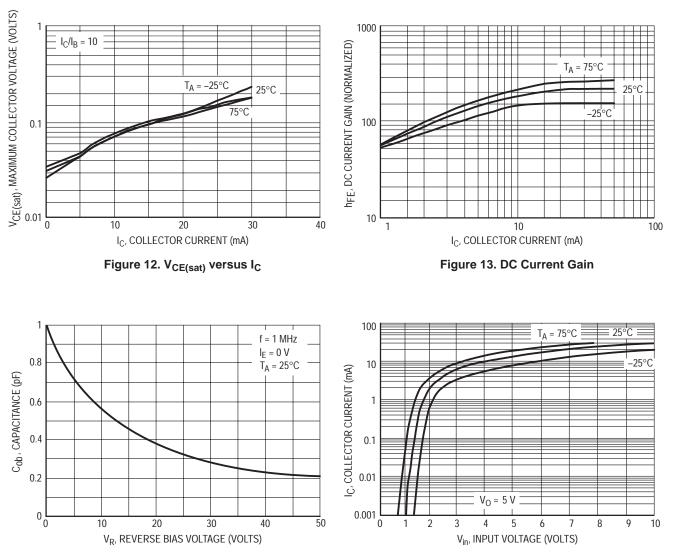


Figure 14. Output Capacitance

Figure 15. Output Current versus Input Voltage

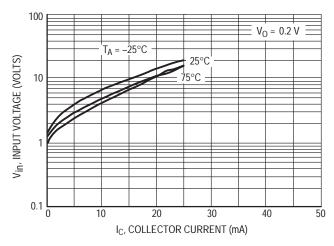


Figure 16. Input Voltage versus Output Current

#### **TYPICAL ELECTRICAL CHARACTERISTICS — MUN5114T1**

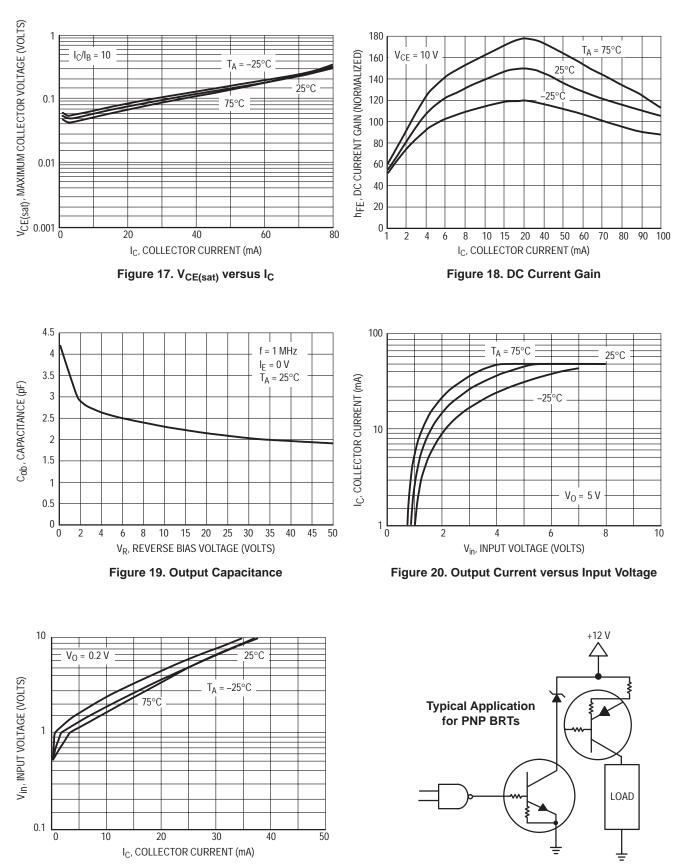


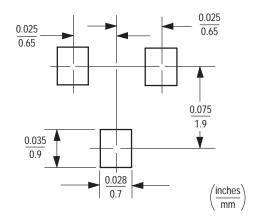
Figure 21. Input Voltage versus Output Current

Figure 22. Inexpensive, Unregulated Current Source

#### MINIMUM RECOMMENDED FOOTPRINTS FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



#### SC-70/SOT-323 POWER DISSIPATION

The power dissipation of the SC–70/SOT–323 is a function of the pad size. This can vary from the minimum pad size for soldering to the pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient; and the operating temperature,  $T_A$ . Using the values provided on the data sheet,  $P_D$  can be calculated as follows:

$$P_{D} = \frac{T_{J(max)} - T_{A}}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values in this case is 150 milliwatts.  $P_{D} = \frac{150^{\circ}C - 25^{\circ}C}{833^{\circ}C/W} = 150 \text{ milliwatts}$ 

into the equation for an ambient temperature T<sub>A</sub> of 25°C,

one can calculate the power dissipation of the device which

The 833°C/W assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 150 milliwatts. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad<sup>™</sup>. Using a board material such as Thermal Clad, a power dissipation of 300 milliwatts can be achieved using the same footprint.

#### SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference should be a maximum of 10°C.

- The soldering temperature and time should not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient should be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling

\* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

#### SOLDER STENCIL GUIDELINES

Prior to placing surface mount components onto a printed circuit board, solder paste must be applied to the pads. A solder stencil is required to screen the optimum amount of solder paste onto the footprint. The stencil is made of brass or stainless steel with a typical thickness of 0.008 inches. The stencil opening size for the surface mounted package should be the same as the pad size on the printed circuit board, i.e., a 1:1 registration.

#### **TYPICAL SOLDER HEATING PROFILE**

For any given circuit board, there will be a group of control settings that will give the desired heat pattern. The operator must set temperatures for several heating zones, and a figure for belt speed. Taken together, these control settings make up a heating "profile" for that particular circuit board. On machines controlled by a computer, the computer remembers these profiles from one operating session to the next. Figure 23 shows a typical heating profile for use when soldering a surface mount device to a printed circuit board. This profile will vary among soldering systems but it is a good starting point. Factors that can affect the profile include the type of soldering system in use, density and types of components on the board, type of solder used, and the type of board or substrate material being used. This profile shows temperature versus time. The line on the graph shows the actual temperature that might be experienced on the surface of a test board at or near a central solder joint. The two profiles are based on a high density and a low density board. The Vitronics SMD310 convection/infrared reflow soldering system was used to generate this profile. The type of solder used was 62/36/2 Tin Lead Silver with a melting point between 177–189°C. When this type of furnace is used for solder reflow work, the circuit boards and solder joints tend to heat first. The components on the board are then heated by conduction. The circuit board, because it has a large surface area, absorbs the thermal energy more efficiently, then distributes this energy to the component may be up to 30 degrees cooler than the adjacent solder joints.

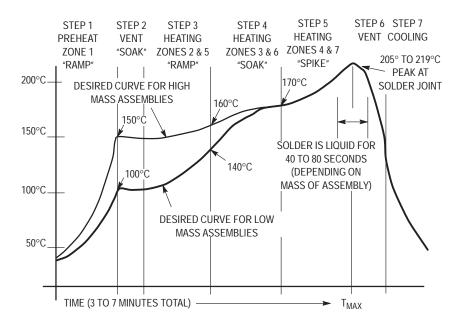
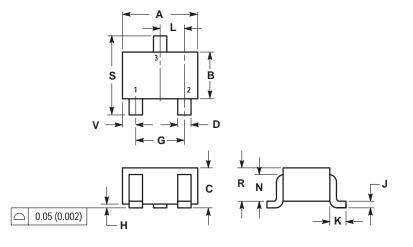


Figure 23. Typical Solder Heating Profile

#### PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-02 ISSUE J



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

|     | INC       | HES   | MILLIN    | ETERS |
|-----|-----------|-------|-----------|-------|
| DIM | MIN       | MAX   | MIN       | MAX   |
| Α   | 0.071     | 0.087 | 1.80      | 2.20  |
| В   | 0.045     | 0.053 | 1.15      | 1.35  |
| С   | 0.035     | 0.049 | 0.90      | 1.25  |
| D   | 0.012     | 0.016 | 0.30      | 0.40  |
| G   | 0.047     | 0.055 | 1.20      | 1.40  |
| Н   | 0.000     | 0.004 | 0.00      | 0.10  |
| J   | 0.004     | 0.010 | 0.10      | 0.25  |
| K   | 0.017     | REF   | 0.425     | REF   |
| L   | 0.026 BSC |       | 0.650 BSC |       |
| Ν   | 0.028     | REF   | 0.700 REF |       |
| R   | 0.031     | 0.039 | 0.80      | 1.00  |
| S   | 0.079     | 0.087 | 2.00      | 2.20  |
| V   | 0.012     | 0.016 | 0.30      | 0.40  |

| STYLE 1:<br>CANCELLED | STYLE 2:<br>PIN 1. ANODE<br>2. N.C.<br>3. CATHODE | STYLE 3:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE | STYLE 5:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE |
|-----------------------|---|---|--|--|
| STYLE 6:              | STYLE 7:  | STYLE 8:  | STYLE 9:   | STYLE 10:  |
| PIN 1. EMITTER        | PIN 1. BASE                                       | PIN 1. GATE   | PIN 1. ANODE   | PIN 1. CATHODE                                     |
| 2. BASE               | 2. EMITTER  | 2. SOURCE   | 2. CATHODE   | 2. ANODE   |
| 3. COLLECTOR          | 3. COLLECTOR                                      | 3. DRAIN  | <ol><li>CATHODE-ANODE</li></ol>                      | <ol><li>ANODE-CATHODE</li></ol>                    |

# **Notes**

Thermal Clad is a trademark of the Bergquist Company

**ON Semiconductor** and without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

#### PUBLICATION ORDERING INFORMATION

#### NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: ONlit@hibbertco.com Fax Response Line: 303–675–2167 or 800–344–3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support

German Phone: (+1) 303–308–7140 (M–F 1:00pm to 5:00pm Munich Time) Email: ONlit–german@hibbertco.com

- French Phone: (+1) 303–308–7141 (M–F 1:00pm to 5:00pm Toulouse Time) Email: ONlit-french@hibbertco.com
- English Phone: (+1) 303–308–7142 (M–F 12:00pm to 5:00pm UK Time) Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS\*: 00-800-4422-3781 \*Available from Germany, France, Italy, England, Ireland

#### CENTRAL/SOUTH AMERICA:

Spanish Phone: 303–308–7143 (Mon–Fri 8:00am to 5:00pm MST) Email: ONlit–spanish@hibbertco.com

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support Phone: 303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time) Toll Free from Hong Kong & Singapore: 001–800–4422–3781 Email: ONlit–asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031 Phone: 81–3–5740–2745 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.